Hideo Hosono

List of Publications by Year in Descending Order

1,227 papers	74,899 citations	119 h-index	241 g-index
1,325 ext. papers	81,820 ext. citations	5.4 avg, IF	8.14 L-index

#	Paper	IF	Citations
1227	Suppression of Rayleigh Scattering in Silica Glass by Codoping Boron and Fluorine: Molecular Dynamics Simulations with Force-Matching and Neural Network Potentials. *Journal of Physical Chemistry C*, **2022**, 126, 2264-2275	3.8	1
1226	Room-Temperature Fast H Conduction in Oxygen-Substituted Lanthanum Hydride.. *Journal of the American Chemical Society*, **2022**,	16.4	3
1225	Fishtail effect and the vortex phase diagram of high-entropy alloy superconductor. *Applied Physics Letters*, **2022**, 120, 092602	3.4	2
1224	Caging-Pnictogen-Induced Superconductivity in Skutterudites IrX (X = As, P).. *Journal of the American Chemical Society*, **2022**,	16.4	1
1223	Degenerated Hole Doping and Ultra-Low Lattice Thermal Conductivity in Polycrystalline SnSe by Nonequilibrium Isovalent Te Substitution.. *Advanced Science*, **2022**, e2105958	13.6	1
1222	Hexagonal BaTiOH Oxyhydride as a Water-Durable Catalyst Support for Chemoselective Hydrogenation.. *Journal of the American Chemical Society*, **2022**,	16.4	2
1221	Characteristic mechanism for fast H□conduction in LaH2.5O0.25. *Acta Materialia*, **2022**, 230, 117825	8.4	0
1220	Pressure-induced reemergence of superconductivity in BaIr2Ge7 and Ba3Ir4Ge16 with cage structures. *Matter and Radiation at Extremes*, **2022**, 7, 038404	4.7	0
1219	Device Modeling and Simulation of TAOS-TFTs **2022**, 369-382		
1218	Solution-Synthesized Metal Oxides and Halides for Transparent p -Channel TFTs **2022**, 539-552		
1217	Transparent Amorphous Oxide Semiconductors for Display Applications **2022**, 1-20		
1216	Tungsten-Doped Active Layers for High-Mobility AOS-TFTs **2022**, 553-575		
1215	Elevated-Metal Metal-Oxide Thin-Film Transistors: A Back-Gate Transistor Architecture with Annealing-Induced Source/Drain Regions **2022**, 273-313		
1214	Oxide TFTs and Their Application to X-Ray Imaging **2022**, 503-517		
1213	Toward the Development of High-Performance p -Channel Oxide-TFTs and All-Oxide Complementary Circuits **2022**, 519-538		
1212	Oxide TFTs for Advanced Signal-Processing Architectures **2022**, 341-368		
1211	Low-Temperature Thin-Film Combustion Synthesis of Metal-Oxide Semiconductors: Science and Technology **2022**, 159-184		

1210 Application of AOSs to Charge Transport Layers in Electroluminescent Devices **2022**, 585-596

1209 Electronic Structure of Transparent Amorphous Oxide Semiconductors **2022**, 73-92

1208 Hot Carrier Effects in Oxide-TFTs **2022**, 315-331

1207 Percolation Description of Charge Transport in Amorphous Oxide Semiconductors: Band Conduction Dominated by Disorder **2022**, 125-144

1206 Transparent Amorphous Oxide Semiconductors **2022**, 21-30 1

1205 Control of Carrier Concentrations in AOSs and Application to Bulk-Accumulation TFTs **2022**, 239-272

1204 Amorphous Oxide Semiconductor TFTs for BEOL Transistor Applications **2022**, 457-472 1

1203 Neuromorphic Chips Using AOS Thin-Film Devices **2022**, 487-501

1202 Electronic Structure and Structural Randomness **2022**, 31-72

1201 Defects and Relevant Properties **2022**, 93-103

1200 Oxide TFT Technology for Printed Electronics **2022**, 405-429

1199 Recent Progress on Amorphous Oxide Semiconductor Thin-Film Transistors Using the Atomic Layer Deposition Technique **2022**, 213-237

1198 Mechanically Flexible Nonvolatile Memory Thin-Film Transistors Using Oxide Semiconductor Active Channels on Ultrathin Polyimide Films **2022**, 431-456

1197 State and Role of Hydrogen in Amorphous Oxide Semiconductors **2022**, 145-157 1

1196 Rare Earth□and Transition Metal□Doped Amorphous Oxide Semiconductor Phosphors for Novel Light-Emitting Diode Displays **2022**, 577-584

1195 Ferroelectric-HfO 2 Transistor Memory with IGZO Channels **2022**, 473-486 0

1194 Carbon-Related Impurities and NBS Instability in AOS-TFTs **2022**, 333-340

1193 Ammonia Decomposition Mediated by Anion Vacancy at the Interface between CaNH with a Rock Salt Structure and Ni Nanoparticle. *Nihon Kessho Gakkaishi*, **2022**, 64, 160-164 0

1192	Catalyst for Ammonia Synthesis; History and Current Status. *Journal of the Institute of Electrical Engineers of Japan*, **2022**, 142, 346-350	0	
1191	Facile Synthesis of TiAC (A = Zn, Al, In, and Ga) MAX Phases by Hydrogen Incorporation into Crystallographic Voids. *Journal of Physical Chemistry Letters*, **2021**, 12, 11245-11251	6.4	0
1190	Mobility–stability trade-off in oxide thin-film transistors. *Nature Electronics*, **2021**, 4, 800-807	28.4	30
1189	Crystalline boron monosulfide nanosheets with tunable bandgaps. *Journal of Materials Chemistry A*, **2021**, 9, 24631-24640	13	3
1188	Breaking of Thermopower-Conductivity Trade-Off in LaTiO Film around Mott Insulator to Metal Transition. *Advanced Science*, **2021**, 8, e2102097	13.6	2
1187	Large phonon drag thermopower boosted by massive electrons and phonon leaking in LaAlO/LaNiO/LaAlO heterostructure. *Nano Letters*, **2021**, 21, 9240-9246	11.5	0
1186	Origin of Metallic Nature of NaN. *Journal of the American Chemical Society*, **2021**, 143, 69-72	16.4	2
1185	Reversible 3D-2D structural phase transition and giant electronic modulation in nonequilibrium alloy semiconductor, lead-tin-selenide. *Science Advances*, **2021**, 7,	14.3	3
1184	Molecular dynamics study on the co-doping effect of Al2O3 and fluorine to reduce Rayleigh scattering of silica glass. *Journal of the American Ceramic Society*, **2021**, 104, 5001-5015	3.8	4
1183	Two-dimensional bipolar ferromagnetic semiconductors from layered antiferromagnets. *Physical Review Materials*, **2021**, 5,	3.2	3
1182	MXene Phase with C3 Structure Unit: A Family of 2D Electrides. *Advanced Functional Materials*, **2021**, 31, 2100009	15.6	2
1181	Crystal and electronic structure engineering of tin monoxide by external pressure. *Journal of Advanced Ceramics*, **2021**, 10, 565-577	10.7	7
1180	High-Entropy van der Waals Materials Formed from Mixed Metal Dichalcogenides, Halides, and Phosphorus Trisulfides. *Journal of the American Chemical Society*, **2021**, 143, 7042-7049	16.4	17
1179	BN and BN Monolayers with High Carrier Mobility and Excellent Optical Performance. *Journal of Physical Chemistry Letters*, **2021**, 12, 4823-4832	6.4	4
1178	Origins of the coloration from structure and valence state of bismuth oxide glasses. *Journal of Non-Crystalline Solids*, **2021**, 560, 120720	3.9	5
1177	2D Electrides: MXene Phase with C3 Structure Unit: A Family of 2D Electrides (Adv. Funct. Mater. 24/2021). *Advanced Functional Materials*, **2021**, 31, 2170174	15.6	
1176	Local Structure Properties of Hydrogenated and Nonhydrogenated Amorphous InGaZnO Thin Films Using XAFS and High-Energy XRD. *Journal of Physical Chemistry C*, **2021**, 125, 13619-13628	3.8	
1175	Electron-Deficient-Type Electride CaPb: Extension of Electride Chemical Space. *Journal of the American Chemical Society*, **2021**, 143, 8821-8828	16.4	4

1174	High-Performance Indium Gallium Tin Oxide Transistors with an AlO Gate Insulator Deposited by Atomic Layer Deposition at a Low Temperature of 150 °C: Roles of Hydrogen and Excess Oxygen in the AlO Dielectric Film. *ACS Applied Materials & Interfaces*, **2021**, 13, 28451-28461	9.5	13
1173	C2 Vacancy-Mediated N2 Activation over Ni-Loaded Rare-Earth Dicarbides for Ammonia Synthesis. *ACS Catalysis*, **2021**, 11, 7595-7603	13.1	2
1172	Chemical stability of hydrogen boride nanosheets in water. *Communications Materials*, **2021**, 2,	6	2
1171	A View on Formation Gap in Transition Metal Hydrides and Its Collapse. *Journal of the American Chemical Society*, **2021**, 143, 11345-11348	16.4	4
1170	Floating Interlayer and Surface Electrons in 2D Materials: Graphite, Electrides, and Electrenes. *Small Science*, **2021**, 1, 2100020		7
1169	How fluorine minimizes density fluctuations of silica glass: Molecular dynamics study with machine-learning assisted force-matching potential. *Materials and Design*, **2021**, 197, 109210	8.1	6
1168	Double Charge Polarity Switching in Sb-Doped SnSe with Switchable Substitution Sites. *Advanced Functional Materials*, **2021**, 31, 2008092	15.6	5
1167	Superconductivity from buckled-honeycomb-vacancy ordering. *Science Bulletin*, **2021**, 66, 327-331	10.6	0
1166	Ruthenium Catalysts Promoted by Lanthanide Oxyhydrides with High Hydride-Ion Mobility for Low-Temperature Ammonia Synthesis. *Advanced Energy Materials*, **2021**, 11, 2003723	21.8	16
1165	Ethanol-ethylene conversion mechanism on hydrogen boride sheets probed by in situ infrared absorption spectroscopy. *Physical Chemistry Chemical Physics*, **2021**, 23, 7724-7734	3.6	7
1164	Ammonia Synthesis: Ruthenium Catalysts Promoted by Lanthanide Oxyhydrides with High Hydride-Ion Mobility for Low-Temperature Ammonia Synthesis (Adv. Energy Mater. 4/2021). *Advanced Energy Materials*, **2021**, 11, 2170018	21.8	0
1163	Ship-in-a-Bottle Synthesis of High Concentration of N Molecules in a Cage-Structured Electride. *Journal of Physical Chemistry Letters*, **2021**, 12, 1295-1299	6.4	2
1162	Why Ca2NH works as an efficient and stable support of Ru catalyst in ammonia synthesis. *Research on Chemical Intermediates*, **2021**, 47, 235-248	2.8	
1161	Stabilization Factor of Anion-Excess Fluorite Phase for Fast Anion Conduction. *Chemistry of Materials*, **2021**, 33, 1867-1874	9.6	5
1160	15.1: Invited Paper: Understanding and controlling electronic defects in amorphous oxide semiconductor. *Digest of Technical Papers SID International Symposium*, **2021**, 52, 97-99	0.5	
1159	Advances in Materials and Applications of Inorganic Electrides. *Chemical Reviews*, **2021**, 121, 3121-3185	68.1	40
1158	Ion Substitution Effect on Defect Formation in Two-Dimensional Transition Metal Nitride Semiconductors, TiN (= Ca, Sr, and Ba). *Inorganic Chemistry*, **2021**, 60, 10227-10234	5.1	0
1157	Ammonia Decomposition over CaNH-Supported Ni Catalysts via an NH2□Vacancy-Mediated Mars□an Krevelen Mechanism. *ACS Catalysis*, **2021**, 11, 11005-11015	13.1	7

1156	Dissociative and Associative Concerted Mechanism for Ammonia Synthesis over Co-Based Catalyst. *Journal of the American Chemical Society*, **2021**, 143, 12857-12866	16.4	8
1155	Unintended Carbon-Related Impurity and Negative Bias Instability in High-Mobility Oxide TFTs. *IEEE Electron Device Letters*, **2021**, 42, 1319-1322	4.4	7
1154	Comment on Weber et al. Mayenite-Based Electride C12A7e□A Reactivity and Stability Study. Catalysts 2021, 11, 334. *Catalysts*, **2021**, 11, 1154	4	
1153	Superconductivity in the Layered Cage Compound Ba3Rh4Ge16. *Chinese Physics Letters*, **2021**, 38, 127402	2.8	1
1152	Electronic Correlation Strength of Inorganic Electrides from First Principles.. *Journal of Physical Chemistry Letters*, **2021**, 12, 12020-12025	6.4	0
1151	High-Performance P-Channel Tin Halide Perovskite Thin Film Transistor Utilizing a 2D-3D Core-Shell Structure.. *Advanced Science*, **2021**, e2104993	13.6	8
1150	Boosting carrier mobility and stability in indium-zinc-tin oxide thin-film transistors through controlled crystallization. *Scientific Reports*, **2020**, 10, 18868	4.9	6
1149	Potential Interaction of Noble Gas Atoms and Anionic Electrons in Ca2N. *Journal of Physical Chemistry C*, **2020**, 124, 12213-12219	3.8	2
1148	p-Type Transparent Quadruple Perovskite Halide Conductors: Fact or Fiction?. *Advanced Functional Materials*, **2020**, 30, 1909906	15.6	11
1147	Pressure-Induced Topological and Structural Phase Transitions in an Antiferromagnetic Topological Insulator. *Chinese Physics Letters*, **2020**, 37, 066401	1.8	16
1146	Heavily Hydride-ion-doped 1111-type Iron-based Superconductors: Synthesis, Physical Properties and Electronic Structure. *Journal of the Physical Society of Japan*, **2020**, 89, 051006	1.5	6
1145	Ferromagnetic quasi-atomic electrons in two-dimensional electride. *Nature Communications*, **2020**, 11, 1526	17.4	25
1144	Phonon scattering limited mobility in the representative cubic perovskite semiconductors SrGeO3, BaSnO3, and SrTiO3. *Physical Review B*, **2020**, 101,	3.3	4
1143	Critical temperature and critical current density of hydrogen-doped SmFeAsO epitaxial films fabricated by thermal annealing with binary hydrides. *Applied Physics Express*, **2020**, 13, 073002	2.4	1
1142	Air-Stable Calcium Cyanamide-Supported Ruthenium Catalyst for Ammonia Synthesis and Decomposition. *ACS Applied Energy Materials*, **2020**, 3, 6573-6582	6.1	11
1141	Anomalous Charge State Evolution and Its Control of Superconductivity in MAlC (M□ Mo, W). *IScience*, **2020**, 23, 101196	6.1	0
1140	Hydrogen Boride Sheets as Reductants and the Formation of Nanocomposites with Metal Nanoparticles. *Chemistry Letters*, **2020**, 49, 789-793	1.7	9
1139	Anisotropic structure of alkali metaphosphate glasses. *Journal of the American Ceramic Society*, **2020**, 103, 3631-3641	3.8	6

1138	Stable single platinum atoms trapped in sub-nanometer cavities in 12CaO·7AlO for chemoselective hydrogenation of nitroarenes. *Nature Communications*, **2020**, 11, 1020	17.4	47
1137	Extraordinary Strong Band-Edge Absorption in Distorted Chalcogenide Perovskites. *Solar Rrl*, **2020**, 4, 1900555	7.1	31
1136	Toward 2D Magnets in the (MnBi Te)(Bi Te) Bulk Crystal. *Advanced Materials*, **2020**, 32, e2001815	24	24
1135	Solid solution for catalytic ammonia synthesis from nitrogen and hydrogen gases at 50 °C. *Nature Communications*, **2020**, 11, 2001	17.4	47
1134	Higher-order topological crystalline insulating phase and quantized hinge charge in topological electride apatite. *Physical Review Research*, **2020**, 2,	3.9	6
1133	Growth, Properties, and Device Fabrication of Iron-Based Superconductor Thin-Films **2020**, 213-241		
1132	Shallow Valence Band of Rutile GeO2 and P-type Doping. *Journal of Physical Chemistry C*, **2020**, 124, 2572-25728	3.8	8
1131	Efficient Ammonia Synthesis over Phase-Separated Nickel-Based Intermetallic Catalysts. *Journal of Physical Chemistry C*, **2020**, 124, 28589-28595	3.8	7
1130	Coexistence of magnetism and superconductivity in thin films of the Fe-based superconductor BaLaFeAs. *Journal of Physics Condensed Matter*, **2020**, 32, 485804	1.8	2
1129	First-Principles and Microkinetic Study on the Mechanism for Ammonia Synthesis Using Ru-Loaded Hydride Catalyst. *Journal of Physical Chemistry C*, **2020**, 124, 2070-2078	3.8	14
1128	Improved polaronic transport under a strong Mott–Hubbard interaction in Cu-substituted NiO. *Inorganic Chemistry Frontiers*, **2020**, 7, 853-858	6.8	3
1127	Transition Metal-doped Ru Nanoparticles Loaded on Metal Hydrides for Efficient Ammonia Synthesis from First Principles. *Journal of Physical Chemistry C*, **2020**, 124, 1529-1534	3.8	2
1126	Geometrical Frustration of B-H Bonds in Layered Hydrogen Borides Accessible by Soft Chemistry. *CheM*, **2020**, 6, 406-418	16.2	20
1125	Strain Engineering at Heterointerfaces: Application to an Iron Pnictide Superconductor, Cobalt-Doped BaFeAs. *ACS Applied Materials & Interfaces*, **2020**, 12, 50096-50104	9.5	2
1124	Computational Prediction of Boron-Based MAX Phases and MXene Derivatives. *Chemistry of Materials*, **2020**, 32, 6947-6957	9.6	34
1123	Vacancy-enabled N activation for ammonia synthesis on an Ni-loaded catalyst. *Nature*, **2020**, 583, 391-395	50.4	129
1122	Intermetallic ZrPd3-Embedded Nanoporous ZrC as an Efficient and Stable Catalyst of the Suzuki Cross-Coupling Reaction. *ACS Catalysis*, **2020**, 10, 14366-14374	13.1	4
1121	A Highly Efficient and Stable Blue-Emitting Cs Cu Cl I with a 1D Chain Structure. *Advanced Materials*, **2020**, 32, e2002945	24	31

1120	Contribution of Nitrogen Vacancies to Ammonia Synthesis over Metal Nitride Catalysts. *Journal of the American Chemical Society*, **2020**, 142, 14374-14383	16.4	39
1119	Magnetism induced by interlayer electrons in the quasi-two-dimensional electride Y2C: Inelastic neutron scattering study. *Physical Review B*, **2020**, 102,	3.3	4
1118	Symmetric Ambipolar Thin-Film Transistors and High-Gain CMOS-like Inverters Using Environmentally Friendly Copper Nitride. *ACS Applied Materials & Interfaces*, **2019**, 11, 35132-35137	9.5	7
1117	Tunable Light Emission through the Range 1.8-3.2 eV and p-Type Conductivity at Room Temperature for Nitride Semiconductors, Ca(MgZn)N (= 0-1). *Inorganic Chemistry*, **2019**, 58, 12311-12316	5.1	6
1116	New Amorphous In□Ga2Zn□O Thin-Film Transistor-Based Optical Pixel Sensor for Optical Input Signal With Short Wavelength. *IEEE Transactions on Electron Devices*, **2019**, 66, 3841-3846	2.9	1
1115	Crystal Structure Built from a GeO6□GeO5 Polyhedra Network with High Thermal Stability: □rGe2O5. *ACS Applied Electronic Materials*, **2019**, 1, 1989-1993	4	2
1114	Amorphous IGZO TFT with High Mobility of ~70 cm/(V s) via Vertical Dimension Control Using PEALD. *ACS Applied Materials & Interfaces*, **2019**, 11, 40300-40309	9.5	88
1113	Insulator-like behavior coexisting with metallic electronic structure in strained FeSe thin films grown by molecular beam epitaxy. *Physical Review B*, **2019**, 99,	3.3	3
1112	Quantum dynamics of hydrogen in the iron-based superconductor LaFeAsO0.9D0.1 measured with inelastic neutron spectroscopy. *Physical Review B*, **2019**, 99,	3.3	1
1111	Pressure-induced quantum critical point in the heavily hydrogen-doped iron-based superconductor LaFeAsO. *Physical Review B*, **2019**, 99,	3.3	2
1110	P-197: Late-News Poster: NBTS-free Oxide TFTs with High Mobility of 40 cm2/Vs: A Possible Origin for NBTS Instability. *Digest of Technical Papers SID International Symposium*, **2019**, 50, 1349-1350	0.5	1
1109	Hydrogen-Insertion-Induced Itinerant Ferromagnetism in Zr2CoH4.8 with Co Chains. *Journal of Physical Chemistry C*, **2019**, 123, 14964-14968	3.8	1
1108	Characteristic fast H ion conduction in oxygen-substituted lanthanum hydride. *Nature Communications*, **2019**, 10, 2578	17.4	38
1107	Discovery of hexagonal ternary phase TiInB and its evolution to layered boride TiB. *Nature Communications*, **2019**, 10, 2284	17.4	72
1106	Acid-durable electride with layered ruthenium for ammonia synthesis: boosting the activity selective etching. *Chemical Science*, **2019**, 10, 5712-5718	9.4	26
1105	Shubnikov□de Haas oscillations in the three-dimensional Dirac fermion system Ca3PbO. *Physical Review B*, **2019**, 99,	3.3	4
1104	Structure and Electronic Properties of [Ca24Al28O64]4+□4e□Surfaces: Opportunities for Termination-Controlled Electron Transfer. *Journal of Physical Chemistry C*, **2019**, 123, 6030-6036	3.8	5
1103	Material Design of Green-Light-Emitting Semiconductors: Perovskite-Type Sulfide SrHfS. *Journal of the American Chemical Society*, **2019**, 141, 5343-5349	16.4	29

1102	Large magnetocaloric effect in van der Waals crystal CrBr3. *Frontiers of Physics*, **2019**, 14, 1	3.7	12
1101	Particulate Generation on Surface of Iron Selenide Films by Air Exposure. *Journal of Superconductivity and Novel Magnetism*, **2019**, 32, 3047-3055	1.5	3
1100	Stabilization and heteroepitaxial growth of metastable tetragonal FeS thin films by pulsed laser deposition. *Superconductor Science and Technology*, **2019**, 32, 054002	3.1	2
1099	Low anisotropic upper critical fields in SmO1⊠ F x FeAs thin films with a layered hybrid structure. *Superconductor Science and Technology*, **2019**, 32, 044003	3.1	11
1098	Pseudogap Control of Physical and Chemical Properties in CeFeSi-Type Intermetallics. *Inorganic Chemistry*, **2019**, 58, 2848-2855	5.1	4
1097	Ternary inorganic electrides with mixed bonding. *Physical Review B*, **2019**, 99,	3.3	17
1096	Electronic Defects in Amorphous Oxide Semiconductors: A Review. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1800372	1.6	103
1095	Transition Metal-Doped Amorphous Oxide Semiconductor Thin-Film Phosphor, Chromium-Doped Amorphous Gallium Oxide. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1800198	1.6	4
1094	On the Origin of the Negative Thermal Expansion Behavior of YCu. *Inorganic Chemistry*, **2019**, 58, 11819-11827	5.1	
1093	Hydrogenated Borophene Shows Catalytic Activity as Solid Acid. *ACS Omega*, **2019**, 4, 14100-14104	3.9	26
1092	Structure and photoelastic constant of binary ns2-type metal cation containing silicate glasses. *Journal of Non-Crystalline Solids*, **2019**, 521, 119526	3.9	8
1091	Intrinsic and Extrinsic Defects in Layered Nitride Semiconductor SrTiN2. *Journal of Physical Chemistry C*, **2019**, 123, 19307-19314	3.8	5
1090	Cation Clustering in Intermetallics: The Modular Bonding Schemes of CaCu and CaCu. *Inorganic Chemistry*, **2019**, 58, 10313-10322	5.1	2
1089	Heteroepitaxial Thin-Film Growth of a Ternary Nitride Semiconductor CaZn2N2. *ACS Applied Electronic Materials*, **2019**, 1, 1433-1438	4	7
1088	Performance boosting strategy for perovskite light-emitting diodes. *Applied Physics Reviews*, **2019**, 6, 031402	17.3	63
1087	Amorphous Oxide Semiconductor Thin-Film Transistors **2019**, 573-587		3
1086	Exotic Crystal Structures and Electronic Structures in Novel Structured Inorganic Materials **2019**, 107-120		
1085	Robust two-gap strong coupling superconductivity associated with low-lying phonon modes in pressurized Nb 5 Ir 3 O superconductors. *Chinese Physics B*, **2019**, 28, 107401	1.2	3

1084	Superconductivity at 48 K of heavily hydrogen-doped SmFeAsO epitaxial films grown by topotactic chemical reaction using CaH2. *Physical Review Materials*, **2019**, 3,	3.2	9
1083	Zeolitic Intermetallics: LnNiSi (Ln = La-Nd). *Journal of the American Chemical Society*, **2019**, 141, 3376-3378	16.4	16
1082	Natural van der Waals heterostructural single crystals with both magnetic and topological properties. *Science Advances*, **2019**, 5, eaax9989	14.3	111
1081	Low-Temperature Synthesis of Perovskite Oxynitride-Hydrides as Ammonia Synthesis Catalysts. *Journal of the American Chemical Society*, **2019**, 141, 20344-20353	16.4	50
1080	Palladium-bearing intermetallic electride as an efficient and stable catalyst for Suzuki cross-coupling reactions. *Nature Communications*, **2019**, 10, 5653	17.4	23
1079	One-step solution synthesis of white-light-emitting films via dimensionality control of the Cs□Cu□ system. *APL Materials*, **2019**, 7, 111113	5.7	43
1078	Ultra-wide bandgap amorphous oxide semiconductors for NBIS-free thin-film transistors. *APL Materials*, **2019**, 7, 022501	5.7	43
1077	Intermetallic Electride Catalyst as a Platform for Ammonia Synthesis. *Angewandte Chemie - International Edition*, **2019**, 58, 825-829	16.4	57
1076	Direct Activation of Cobalt Catalyst by 12CaO·7Al2O3 Electride for Ammonia Synthesis. *ACS Catalysis*, **2019**, 9, 1670-1679	13.1	46
1075	Superconducting transition temperatures in the electronic and magnetic phase diagrams of SrVFeAsO , a superconductor. *Journal of Physics Condensed Matter*, **2019**, 31, 115801	1.8	6
1074	Multiple Color Inorganic Thin-Film Phosphor, RE-Doped Amorphous Gallium Oxide (RE = Rare Earth: Pr, Sm, Tb, and Dy), Deposited at Room Temperature. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1700833	1.6	11
1073	Effects of Base Pressure on Growth and Optoelectronic Properties of Amorphous In-Ga-Zn-O: Ultralow Optimum Oxygen Supply and Bandgap Widening. *Physica Status Solidi (A) Applications and Materials Science*, **2019**, 216, 1700832	1.6	11
1072	High Electron Density on Ru in Intermetallic YRu2: The Application to Catalyst for Ammonia Synthesis. *Journal of Physical Chemistry C*, **2018**, 122, 10468-10475	3.8	31
1071	Structural Series in the Ternary A-Mn-As System (A = Alkali Metal): Double-Layer-Type CsMnAs and RbMnAs and Tunnel-Type KMnAs. *Inorganic Chemistry*, **2018**, 57, 4997-5003	5.1	2
1070	Large Oblate Hemispheroidal Ruthenium Particles Supported on Calcium Amide as Efficient Catalysts for Ammonia Decomposition. *Chemistry - A European Journal*, **2018**, 24, 7976-7984	4.8	24
1069	Superconductivity induced by field-driven proton injection. *Science Bulletin*, **2018**, 63, 5-6	10.6	2
1068	Material Design of p-Type Transparent Amorphous Semiconductor, Cu-Sn-I. *Advanced Materials*, **2018**, 30, e1706573	24	46
1067	Role of fluorine in two-dimensional dichalcogenide of SnSe. *Scientific Reports*, **2018**, 8, 1645	4.9	8

1066	Self-organized Ruthenium-Barium Core-Shell Nanoparticles on a Mesoporous Calcium Amide Matrix for Efficient Low-Temperature Ammonia Synthesis. *Angewandte Chemie*, **2018**, 130, 2678-2682	3.6	18
1065	Self-organized Ruthenium-Barium Core-Shell Nanoparticles on a Mesoporous Calcium Amide Matrix for Efficient Low-Temperature Ammonia Synthesis. *Angewandte Chemie - International Edition*, **2018**, 57, 2648-2652	16.4	98
1064	Ternary intermetallic LaCoSi as a catalyst for N2 activation. *Nature Catalysis*, **2018**, 1, 178-185	36.5	149
1063	Roles of Pseudo-Closed s Orbitals for Different Intrinsic Hole Generation between Tl-Bi and In-Bi Bromide Double Perovskites. *Journal of Physical Chemistry Letters*, **2018**, 9, 258-262	6.4	23
1062	Material Design of Transparent Oxide Semiconductors for Organic Electronics: Why Do Zinc Silicate Thin Films Have Exceptional Properties?. *Advanced Electronic Materials*, **2018**, 4, 1700352	6.4	14
1061	Doping Induced Polymorph and Carrier Polarity Changes in LaSeF. *Chemistry of Materials*, **2018**, 30, 597-601	9.6	2
1060	Optical and Electrical Properties of Perovskite Variant (CH3NH3)2SnI6. *Journal of Physical Chemistry C*, **2018**, 122, 10749-10754	3.8	28
1059	CsFeSe: A Compound Closely Related to Alkali-Intercalated FeSe Superconductors. *Inorganic Chemistry*, **2018**, 57, 4502-4509	5.1	7
1058	Recent advances in iron-based superconductors toward applications. *Materials Today*, **2018**, 21, 278-302	21.8	200
1057	Pulsed laser deposition of SmFeAsO1−xFx on MgO(100) substrates. *Applied Surface Science*, **2018**, 437, 418-423	6.7	8
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